

## **Information Disclosure Statement**

New U.S. Patent Application for  
METHOD FOR FORMING CAPACITOR IN SEMICONDUCTOR DEVICE  
Our Ref. No.: P03H1019/US/iw

Reference No.:

- (1) US Patent No. 6,489,214
- (2) US Patent No. 6,144,060
- (3) US Publication No. 2002/0020869 A1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

YONG-SOO KIM

Application No.:

Filed:

For: **Method For Forming Capacitor In  
Semiconductor Device**

Art Group:

Examiner:

**INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Date: \_\_\_\_\_

7/17/03

  
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